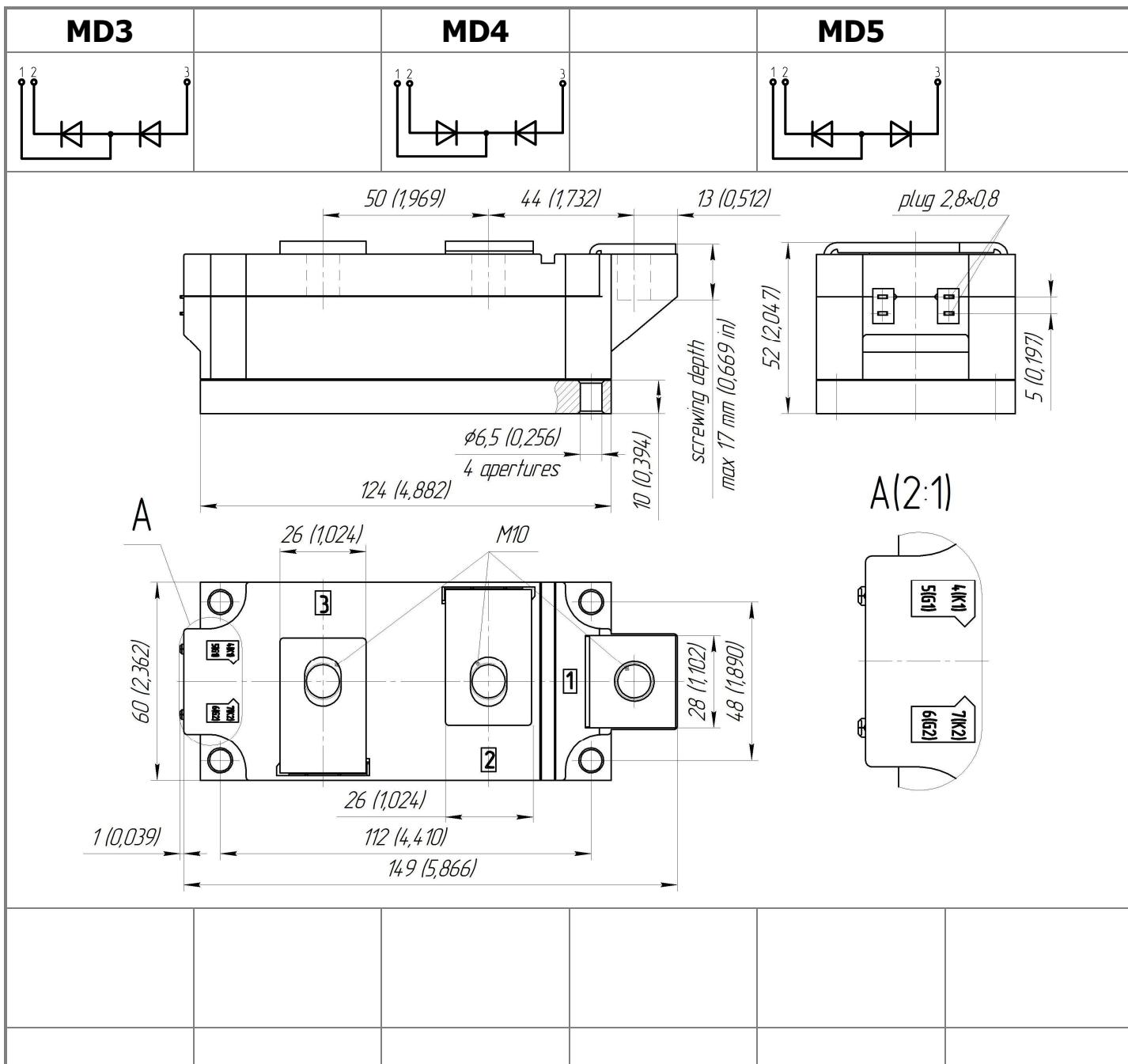




Electrically isolated base plate
 Industrial standard package
 Simplified mechanical design, rapid assembly
 Pressure contact

Double Diode Module For Phase Control **MDx-660-18-A2**

Average forward current	I _{FAV}	660 A			
Repetitive peak reverse voltage	V _{RRM}	1000 ÷ 1800 V			
V _{RRM} , V	1000	1200	1400	1600	1800
Voltage code	10	12	14	16	18
T _j , °C	- 40 ÷ 150				



All dimensions in millimeters (inches)

MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
ON-STATE					
I _{FAV}	Average forward current	A	660	T _c =100 °C;	
I _{FRMS}	RMS forward current	A	1036	180° half-sine wave; 50 Hz	
I _{FSM}	Surge forward current	kA	19.0 22.0	T _j =T _j max; T _j =25 °C	180° half-sine wave; 50 Hz (t _p =10 ms); single pulse; V _R =0 V;
			20.0 23.0	T _j =T _j max; T _j =25 °C	180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _R =0 V;
I ² t	Safety factor	A ² s·10 ³	1805 2420	T _j =T _j max; T _j =25 °C	180° half-sine wave; 50 Hz (t _p =10 ms); single pulse; V _R =0 V;
			1660 2195	T _j =T _j max; T _j =25 °C	180° half-sine wave; 60 Hz (t _p =8.3 ms); single pulse; V _R =0 V;
BLOCKING					
V _{RRM}	Repetitive peak reverse voltages	V	1000÷1800	T _{j min} < T _j <T _j max;	180° half-sine wave; 50 Hz;
V _{RSM}	Non-repetitive peak reverse voltages	V	1100÷1900	T _{j min} < T _j <T _j max;	180° half-sine wave; 50 Hz; single pulse;
V _R	Reverse continuous voltages	V	0.75V _{RRM}	T _j =T _j max;	
THERMAL					
T _{stg}	Storage temperature	°C	-40 ÷ 125		
T _j	Operating junction temperature	°C	-40 ÷ 150		
MECHANICAL					
a	Acceleration under vibration	m/s ²	50		

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions
ON-STATE				
V _{FM}	Peak forward voltage, max	V	1.40	T _j =25 °C; I _{FM} =1978 A
V _{F(TO)}	Forward threshold voltage, max	V	0.78	T _j =T _j max;
r _T	Forward slope resistance, max	mΩ	0.230	0.5 π I _{FAV} < I _T < 1.5 π I _{FAV}
BLOCKING				
I _{RRM}	Repetitive peak reverse current, max	mA	50	T _j =T _j max; V _R =V _{RRM}
THERMAL				
R _{thjc}	Thermal resistance, junction to case			
	per module	°C/W	0.0325	180° half-sine wave, 50 Hz
	per arm	°C/W	0.0650	
	per module	°C/W	0.0310	
	per arm	°C/W	0.0620	DC
R _{thch}	Thermal resistance, case to heatsink			
	per module	°C/W	0.0100	
	per arm	°C/W	0.0200	
INSULATION				
V _{ISOL}	Insulation test voltage	kV	3.00	Sine wave, 50 Hz;
			3.60	t=1 min RMS t=1 sec
MECHANICAL				
M ₁	Mounting torque (M6) ¹⁾	Nm	6.00	Tolerance ± 15%
M ₂	Terminal connection torque (M10) ¹⁾	Nm	12.00	Tolerance ± 15%
w	Weight	g	1500	

PART NUMBERING GUIDE										NOTES
MD 3 - 660 - 18 - A2 - N 1 2 3 4 5 6										1) The screws must be lubricated
1. MD - Rectifier Diode 2. Circuit Schematic: 3 – serial connection 4 – common Cathode 5 – common Anode 3. Average Forward Current, A 4. Voltage Code 5. Package Type (M.A2) 6. Ambient Conditions: N – Normal										



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